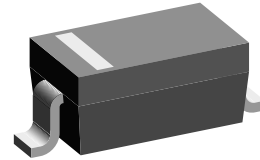


Small Signal Schottky Diode

Features

- These diodes feature very low turn-on voltage and fast switching
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



17431

Mechanical Data

Case: SOD123 Plastic case

Weight: approx. 10.3 mg

Packaging Codes/Options:

GS18/10 k per 13" reel (8 mm tape), 10 k/box

GS08/3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Ordering code	Type Marking	Remarks
BAT54W-V	BAT54W-V-GS18 or BAT54W-V-GS08	L4	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V_{RRM}	30	V
Forward continuous current	$T_{amb} = 25\text{ }^{\circ}\text{C}$	I_F	200 ¹⁾	mA
Repetitive peak forward current	$t_p < 1\text{ s}$, $\delta < 0.5$, $T_{amb} = 25\text{ }^{\circ}\text{C}$	I_{FRM}	300 ¹⁾	mA
Surge forward current	$t_p < 10\text{ ms}$, $T_{amb} = 25\text{ }^{\circ}\text{C}$	I_{FSM}	600 ¹⁾	mA
Power dissipation ¹⁾	$T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	150 ¹⁾	mW

¹⁾ Valid provided that electrodes are kept at ambient temperature

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R_{thJA}	650 ¹⁾	K/W
Maximum junction temperature		T_j	125	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	tested with 100 μA pulses	$V_{(BR)}$	30			V
Leakage current ²⁾	$V_R = 25\text{ V}$	I_R			2	μA
Forward voltage ²⁾	$I_F = 0.1\text{ mA}$	V_F			240	mV
	$I_F = 1\text{ mA}$	V_F			320	mV
	$I_F = 10\text{ mA}$	V_F			400	mV
	$I_F = 30\text{ mA}$	V_F			500	mV
	$I_F = 100\text{ mA}$	V_F			800	mV
Diode capacitance	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_D			10	pF
Reverse recovery time	$I_F = I_R = 10\text{ mA}$; $I_R = 1\text{ mA}$; $R_L = 100\ \Omega$	t_{rr}			5	ns

²⁾ Pulse test: $t_p < 300\ \mu\text{s}$, $\theta < 2\%$

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

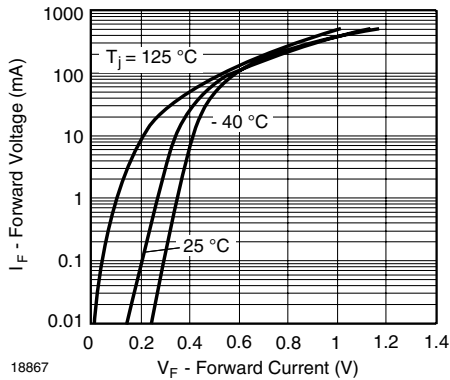


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

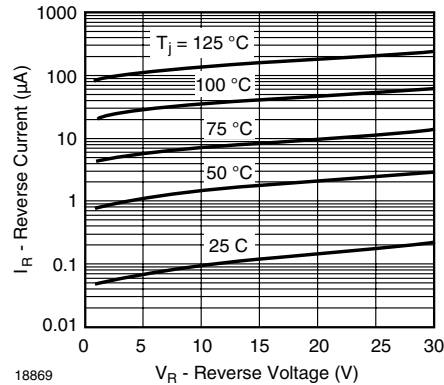


Figure 3. Typical Variation of Reverse Current at Various Temperatures

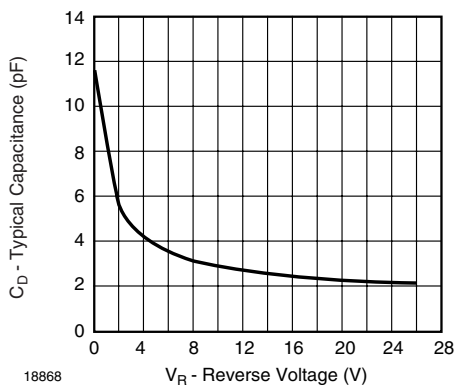


Figure 2. Typical Capacitance $^{\circ}\text{C}$ vs. Reverse Applied Voltage V_R

Package Dimensions in mm (Inches)

